

Progress in fabrication of high quality Tantalum film absorber for STJ radiation detector.



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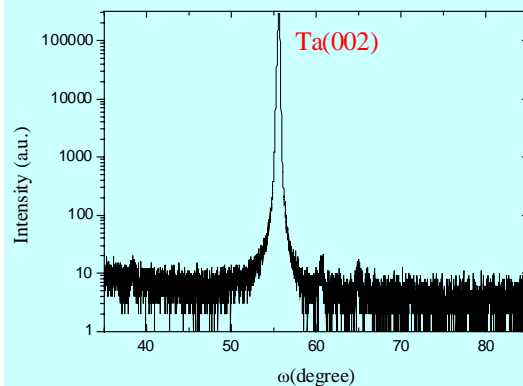
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Deposition methods: magnetically-enhanced dc-triode sputtering
Substrates: R-plane single crystal sapphire at $T=800^\circ$

RRR= 75
 $T_c=4.5 \pm 0.1K$
 $\Delta T_c=0.01K$



Ta absorber with lateral Al-STJs

